

2N916

JAN AVAILABLE
CASE 22, STYLE 1
TO-18 (TO-206AA)

GENERAL PURPOSE
TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	0.36 2.06	Watts $\text{mW}/^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.2 6.9	Watts $\text{mW}/^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

Refer to 2N3946 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage(1) ($I_C = 30\text{ mA}, I_B = 0$)	$V_{CEO(sus)}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	45	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu\text{A}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30\text{ V}, I_E = 0$)	I_{CBO}	—	10	nAdc
Collector Cutoff Current @ 150°C ($V_{CB} = 30\text{ V}, I_E = 0$)	I_{CBO}	—	10	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$) ($I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}, -55^\circ\text{C}$)	h_{FE}	50 15	200 —	—
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 5.0\text{ V}, I_E = 0$)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ V}, I_C = 0$)	C_{ibo}	—	10	pF
Input Impedance, $f = 1.0\text{ kHz}$ ($I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}$) ($I_C = 5.0\text{ mA}, V_{CE} = 5.0\text{ V}$)	h_{ie}	— —	6000 2000	ohms ohms
Small-Signal Current Gain, $f = 1.0\text{ kHz}$ ($I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}$) ($I_C = 5.0\text{ mA}, V_{CE} = 5.0\text{ V}$)	h_{fe}	40 50	200 250	—
Magnitude of Forward Circuit Transfer Ratio, Common-Emitter ($I_C = 10\text{ mA}, V_{CE} = 15\text{ V}$)	$ h_{fe} $	3.0	—	—
Output Admittance, $f = 1.0\text{ kHz}$ ($I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}$) ($I_C = 5.0\text{ mA}, V_{CE} = 5.0\text{ V}$)	h_{oe}	— —	75 125	μmho μmho
Collector Base Time Constant ($I_C = 10\text{ mA}, V_{CB} = 10\text{ V}, f = 40\text{ MHz}$)	$rb' C_c$	—	300	ps

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 1.0\%$.